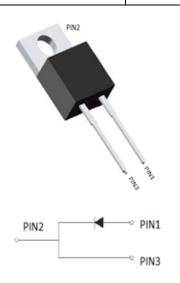


YJD112005PG1



Silicon Carbide Schottky Diode

V_{RRM}	1200V
I _{F (135°C)}	7.5A
Qc	37nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

• Package: TO-220

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_c=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE	
Device marking code			D112005PG1	
Reverse voltage (repetitive peak) @ T _j =25°C	V_{RRM}	V	1200	
Reverse voltage (Surge Peak) @ T _j =25°C	V_{RSM}	V	1200	
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	1200	
Continuous forward current @ T _c =25°C			17	
Continuous forward current @ T _c =135°C	I _F	I _F	Α	7.5
Continuous forward current @ T₀=152°C			5	
Non-repetitive peak forward surge current @ T _c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	Α	52	
Power Dissipation@ T _c =25°C	_		79	
Power Dissipation@ T₀=110°C	Р _{тот}	W	34	
i²t Value@ Tc=25°C ,tp=10ms	∫ i²dt	A ² S	13	
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175	

YJD112005PG1

■Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	V _F	V	I _F =5A, T _j =25°C	1.4	1.57
			I _F =5A, T _j =175°C	2.0	-
Reverse leakage current	I _R	μА	V _R =1200V, T _j =25°C	1.8	16
			V _R =1200V, T _j =175°C	10	-
Total capacitive charge	Qc	nC	V_R =800V, T_j =25°C, QC = $\int_0^{VR}C(V)dV$	37	
Total capacitance	С	pF	V _R =0V, f=1MHZ	410	-
			V _R =400V, f=1MHZ	35	-
			V _R =800V, f=1MHZ	27	-
Capacitance Stored Energy	Ec	μJ	V _R =800V	10	-

■Thermal Characteristics $(T_a=25$ $^{\circ}$ C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{\theta J\text{-}C}$	°C W	1.9

■Typical Characteristics

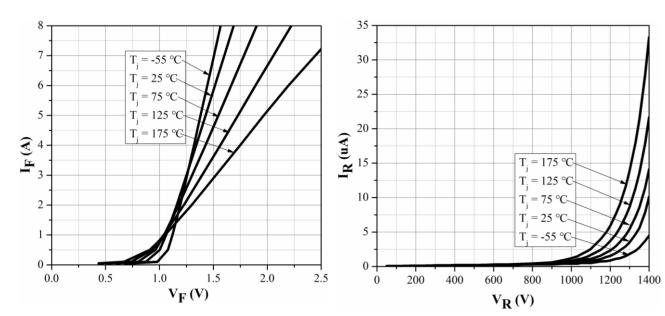


Figure 1. Forward Characteristics

Figure 2. Reverse Characteristic





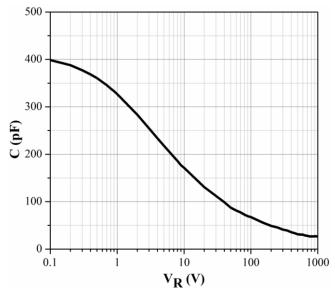


Figure 3. Capacitance vs. Reverse Voltage

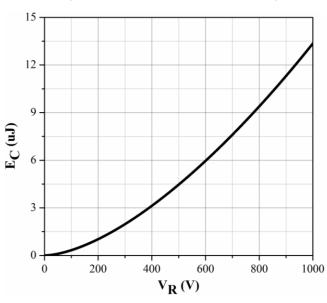
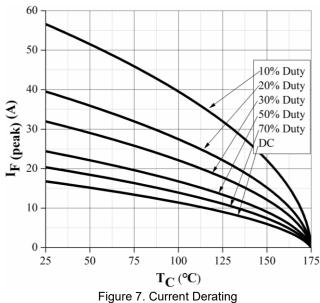


Figure 5. Capacitance Stored Energy



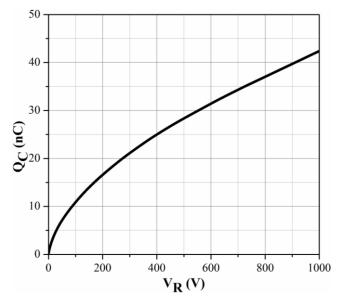


Figure 4. Total Capacitance Charge vs. Reverse Voltage

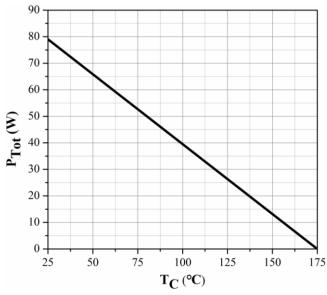


Figure 6. Power Derating

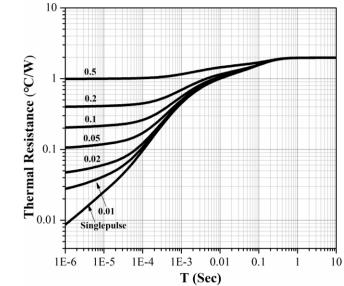


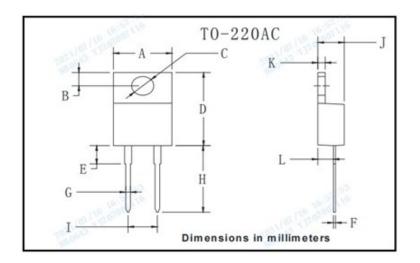
Figure 8. Transient Thermal Impedance







■Outline Dimensions



TO-220AC				
Dim	Min	Max		
Α	9.95	10.35		
В	2.55	2.95		
С	3.75	4.05		
D	14.95	15.25		
Е	3.75	4.25		
F	0.26	0.5		
G	0.68	0.94		
Н	13.3	13.9		
I	4.86	5.26		
J	4.38	4.78		
K	1.14	1.4		
L	2.37	2.79		



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